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Author and Subject Index
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The Computer-Derived 1977 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles, reviews, brief communications, discussions, and news and reviews listed in the contents pages. They do not include meeting papers, abstracts, and news items. These indices were prepared for the *Journal* by the Institute for Scientific Information®, Philadelphia, Pennsylvania.

Using the Index

1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or, if he is a secondary author, to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, B13 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name. This truncation is indicated by a period at the end of the last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

NEWTON SCHWARTZ
Chairman
Publication Committee

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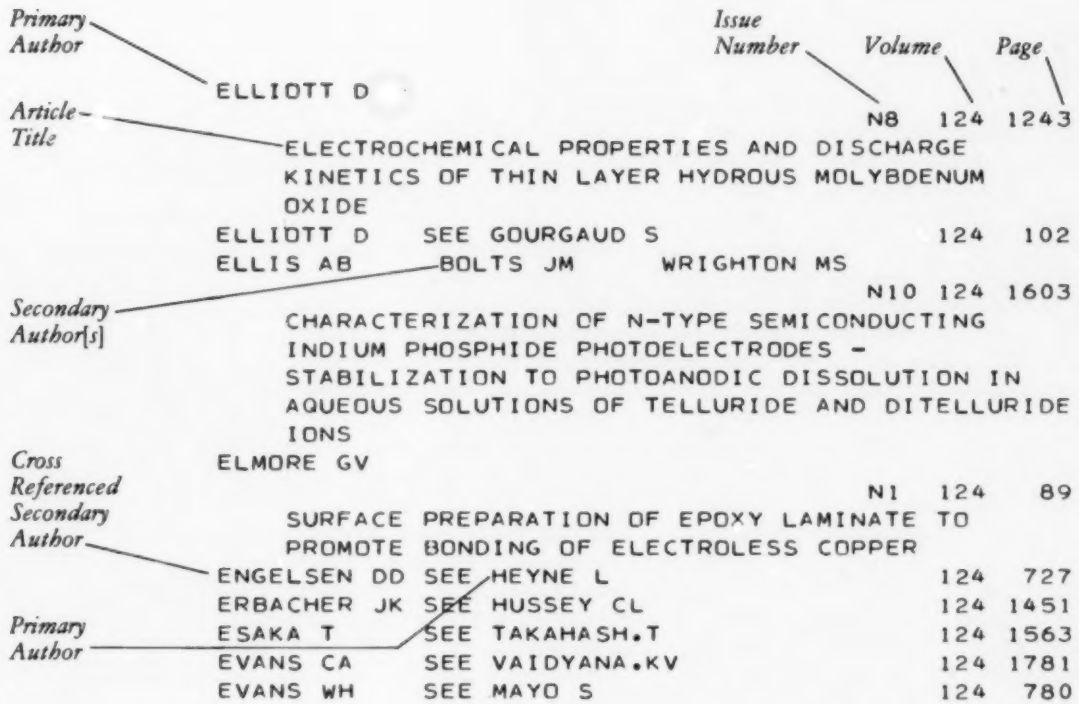
AUTHOR AND TITLE INDEX

To locate a full description of a source item, look up the primary author. Under a given name, journal articles or primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.



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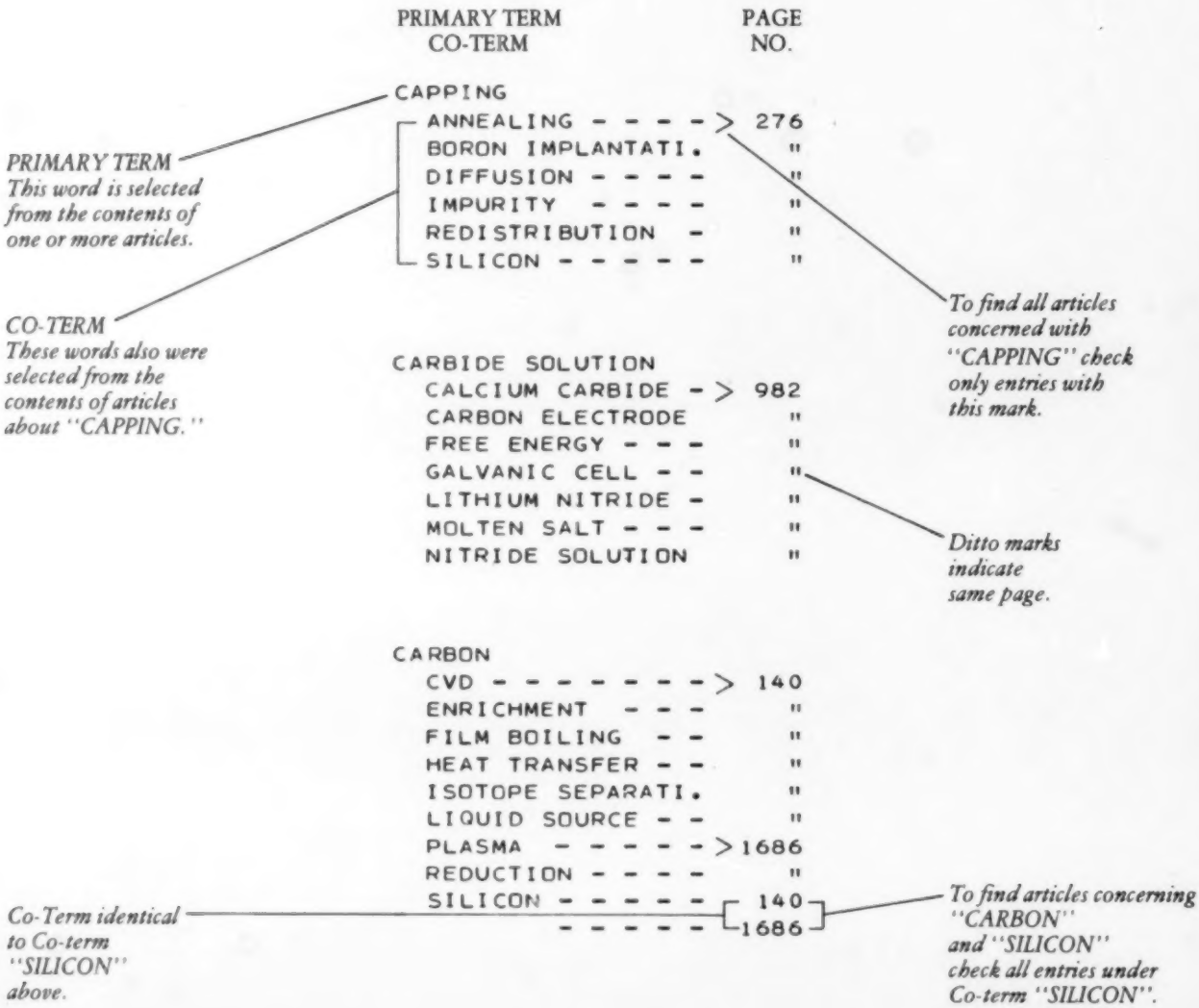
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Announcement

To decrease costs and improve the use of the annual and decennial indexes, the author-chosen random key words is being abandoned starting in 1978. Instead, the following Standard Key-Descriptor List will be used. Each author should follow the instructions below for the proper selection.

Standard Key-Descriptor List

A selection of no more than four standard key-descriptors from the attached list is required for each JOURNAL article. These descriptors are used for the yearly and decennial indexes.

These descriptors are divided into four classes: Material, Component or System, Electrical or Optical Phenomena and Techniques, Chemical or Physical or Other Phenomena and Techniques. The author should tend to select one descriptor from each of these classes with a maximum of four. Avoid selection of all descriptors from a single class. Words appearing in the title should be avoided since they are the prime source of other important descriptors.

The key-descriptors are purposefully general in order to control the over-all size of the JOURNAL index and thereby reduce costs. Specificity is determined by the author in the judicious choice of the article title.

Standard Key-Descriptors

I	II	III	IV
"Material"	Component, System	Electrical/Optical Phenomena-Techniques	Chemical/Physical/Other Phenomena-Techniques
Abrasive	Amplifier	Acoustics	Absorption
Acid	Anode	Antiferroelectricity	Activation
Additives			Activity Coeff.
Adhesives			Additive
Addresses			Adsorption
Aerosol			Allotrophy
Air			Analysis
Alloy			Anneal
Amalgam			Association
Amorphous			Azcotropes
Anion			
Atmosphere			
	Battery		Biological
			Boiling
			Bonding
Carbon	Capacitor	Capacitance	Catalysis
Cations	Cathode	Candoluminescence	Chelation
Ceramics	Cell	Cathodoluminescence	Chemisorption
Chelates	Circuits	Charge	Chromatography
Cleaners	Coils	Chemiluminescence	Chronopotentiometry
Coatings	Computer	Coercive Force	Coagulation
Colorants	Connectors	Conductance	Condensation
Composites	Contacts	Current	Conduction
	Couplers	Current Density	Contamination
	Cryotrons	Current Efficiency	Convection
		Crystallography	Cooling
			Corrosion
			Cracking
			Crystallization
			CVD
Defects	Diodes	Depolarization	Deposition
Dendrite		Discharge	Desorption
Dielectrics			Dialysis
			Diffraction
			Diffusion
			Dipole
			Discharge
			Dissolution
			Dissociation
			Doping
			DTA
Electret	Electrode	Electroluminescence	Economics
Electrolyte		Electrostatics	Effusion
Electron		Ellipsometry	Electrodeposition
Emulsion		EPR	Electrodialysis
Environment		ESCA	Electroless
Eutectic		ESR	Electrolysis